

SNS COLLEGE OF ENGINEERING

Coimbatore-641 107 (An Autonomous Institution)

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DEPARTMENT OF PHYSICS

COURSE NAME : 19PY101-ENGINEERING PHYSICS

I YEAR / I SEMESTER

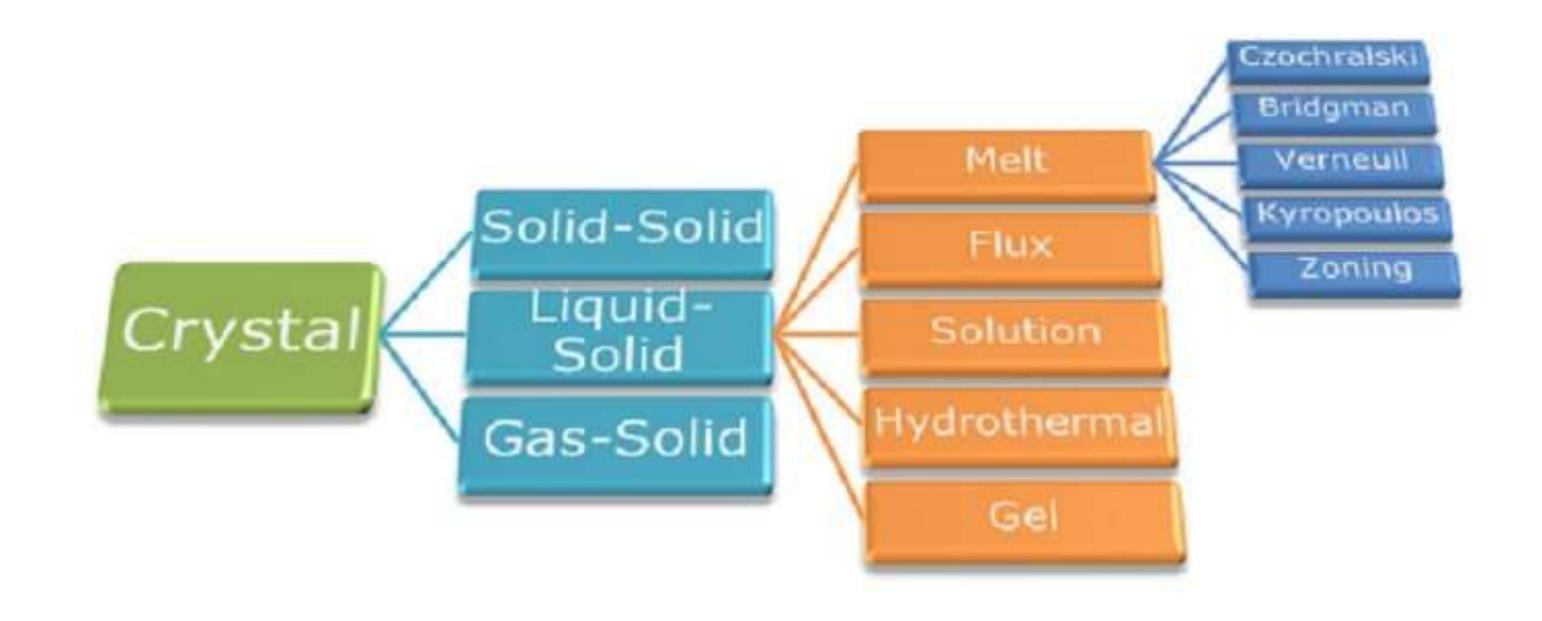
UNIT 4 – CRYSTAL PHYSICS

TOPIC 9 – GROWTH OF SINGLE CRYSTALS MELT GROWTH TECHNIQUES

(CZOCHRALSKI METHOD)







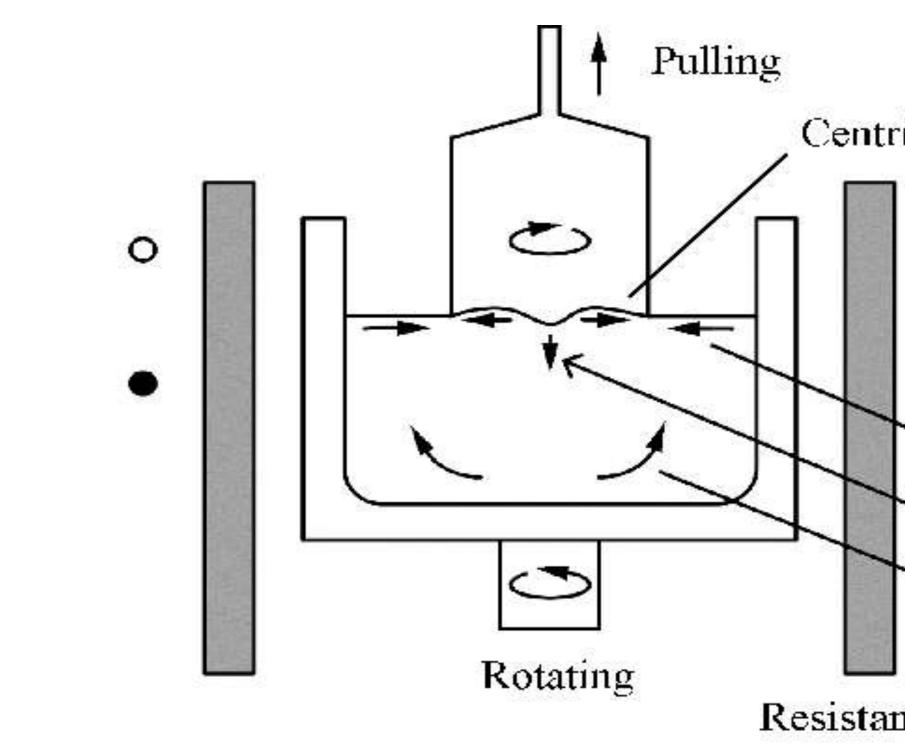




 \succ One of the major melt-growth techniques. \succ It is widely used for growing large-size single crystals for a wide range of commercial and technological applications. \succ One of the main advantages of Czochralski method is the relatively high growth rate.









Centrifugal force

Coil

O Surface tension

Lorentz force

Buoyancy

Resistance heating



 \succ The material to be grown is first melted by induction or resistance heating under a controlled atmosphere in a non-reacting crucible. \succ The melt is kept for a certain time at a temperature above the melting point and the temperature is then reduced to a value slightly above the freezing point.





>The freezing point is judged by cooling the melt until crystals start to appear on the surface.

 \succ After a further lowering of the temperature a seed (cut in the appropriate) orientation) is inserted into the melt.

 \succ By pulling and rotating the seed simultaneously a crystallization center forms.

 \succ The diameter of the pulled crystal is controlled by manipulating the temperature of the melt and the pulling rate.

> Suitable engineering of both axial and radial temperature gradients is needed to grow single crystals of desired dimensions reliably.





Important factors

- 1. The Pulling rate of the crystal
- 2. Temperature gradient of crystal
- 3. Temperature of the melt







Advantages :

- 1. Large diameter of crystal as 10cm or more can be obtained with a more crystal growth rate.
- 2. Crystal with desired orientation can be grown if a seed crystal at that particular orientation is used.
- 3.For the crystal growth adjustment in temperature and growing rate can be made if needed.
- 4. Dopant distribution is quite uniform.





Disadvantage:

More defects and stresses are introduced when the crystal are grown as larger diameter.





References

•https://www.alineason.com/en/knowhow/crystalgrowth/ •https://images.app.goo.gl/Ach4ca4jXkBLXoS97



GROWTH OF SINGLE CRYSTALS MELT GROWTH TECHNIQUES /19PY101-CRYSTAL PHYSICS/B.VIJAYAKUMAR/PHYSICS/SNSCE



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